NCE N-Channel Super Trench Power MOSFET

Description

The NCEP1580 uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

General Features

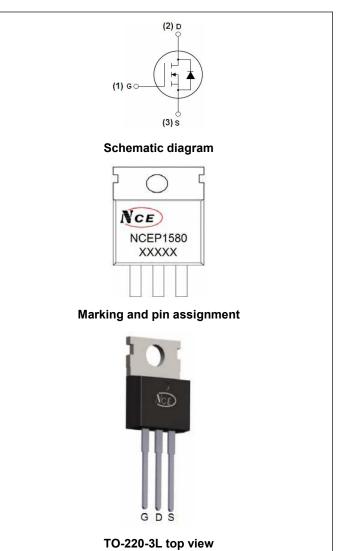
- $V_{DS} = 150V, I_{D} = 80A$ $R_{DS(ON)} < 12.5 m\Omega @ V_{GS} = 10V$
- Excellent gate charge x R_{DS(on)} product(FOM)
- Very low on-resistance R_{DS(on)}
- 175 °C operating temperature
- Pb-free lead plating
- 100% UIS tested

Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

100% UIS TESTED!

100% ΔVds TESTED!



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP1580	NCEP1580	TO-220-3L	-	-	-

Absolute Maximum Ratings (T_c=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	150	V
Gate-Source Voltage	Vgs	±20	V
Drain Current-Continuous	I _D	80	А
Drain Current-Continuous(T _C =100 °C)	I _D (100°C)	56.6	Α
Pulsed Drain Current	I _{DM}	320	Α
Maximum Power Dissipation	P _D	210	W
Derating factor		1.4	W/℃
Single pulse avalanche energy (Note 1)	E _{AS}	980	mJ
Operating Junction and Storage Temperature Range	T_{J}, T_{STG}	-55 To 175	°C



Thermal Characteristic

		Thermal Resistance, Junction-to-Case	Rejc	0.71	°C/W
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Electrical Characteristics (T_C=25°C unless otherwise noted)

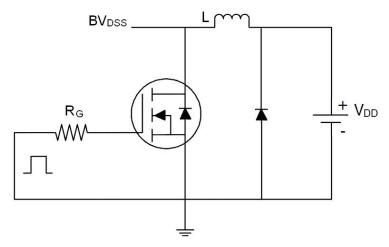
Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics	,					
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	150		-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =150V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V_{GS} =±20 V , V_{DS} =0 V	-	-	±100	nA
On Characteristics			•			
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS},I_{D}=250\mu A$	2.5	-	4.5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =40A	-	10.4	12.5	mΩ
Forward Transconductance	g FS	V _{DS} =5V,I _D =20A	28	-	-	S
Dynamic Characteristics			•	'		•
Input Capacitance	C _{lss})/ 75\/\\ 0\/	-	3200	-	PF
Output Capacitance	Coss	$V_{DS}=75V, V_{GS}=0V,$	-	382	-	PF
Reverse Transfer Capacitance	Crss	F=1.0MHz	-	17.9	-	PF
Switching Characteristics (Note 2)						•
Turn-on Delay Time	t _{d(on)}		-	17	-	nS
Turn-on Rise Time	t _r	V_{DD} =75 V , I_{D} =40 A	-	35	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10 V , R_{G} =4.7 Ω	-	32	-	nS
Turn-Off Fall Time	t _f		-	9	-	nS
Total Gate Charge	Qg	V _{DS} =75V,I _D =40A,	-	44.1		nC
Gate-Source Charge	Q _{gs}		-	14.8		nC
Gate-Drain Charge	Q _{gd}	V _{GS} =10V	-	10.5		nC
Drain-Source Diode Characteristics			•			
Diode Forward Voltage	V _{SD}	V _{GS} =0V,I _S =80A	-		1.2	V
Diode Forward Current	Is		-	-	80	Α
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F = I _S	-	140		nS
Reverse Recovery Charge	Qrr	di/dt = 100A/µs	-	214		nC

Notes:

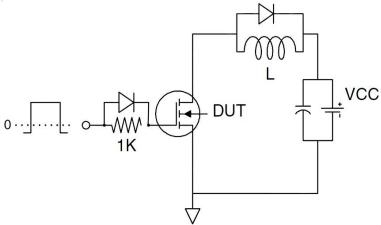
- 1. EAS condition : Tj=25 $^{\circ}\text{C}$,V_DD=50V,V_G=10V,L=0.5mH,Rg=25 Ω
- 2. Guaranteed by design, not subject to production
- 3. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsin k, assuming a maximum junction temperature of TJ(MAX)=175° C. The SOA curve provides a single pulse rating.

Test Circuit

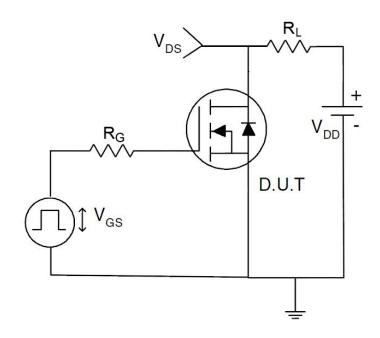
1) E_{AS} test Circuit



2) Gate charge test Circuit



3) Switch Time Test Circuit





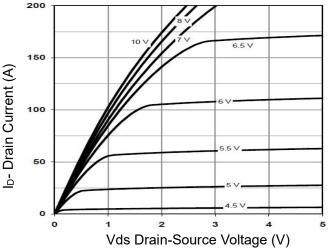


Figure 1 Output Characteristics

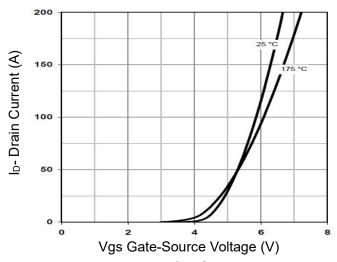


Figure 2 Transfer Characteristics

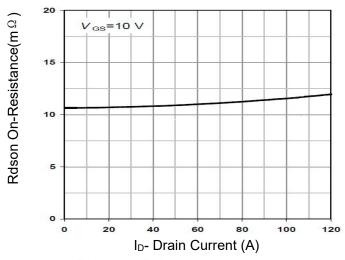


Figure 3 Rdson- Drain Current

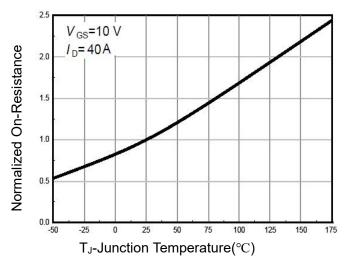


Figure 4 Rdson-JunctionTemperature

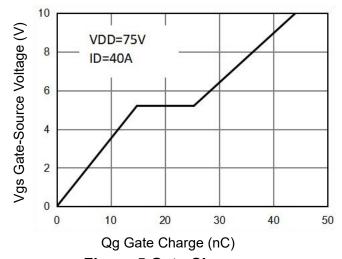


Figure 5 Gate Charge

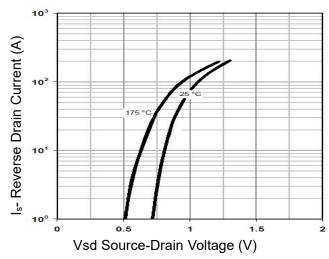
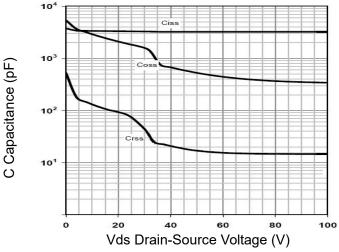


Figure 6 Source- Drain Diode Forward





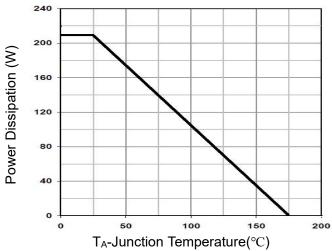
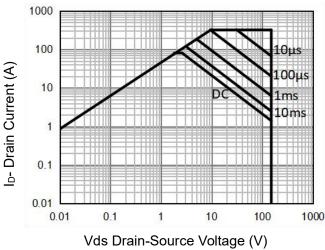


Figure 7 Capacitance vs Vds

Figure 9 Power De-rating



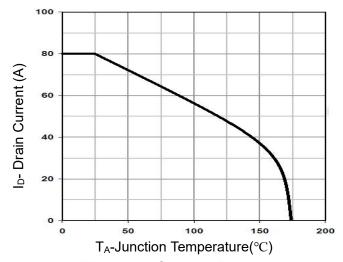


Figure 8 Safe Operation Area(Note3)

Figure 10 Current De-rating

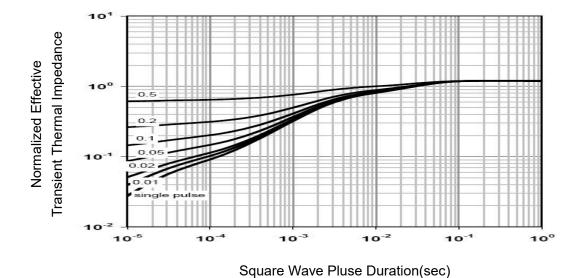
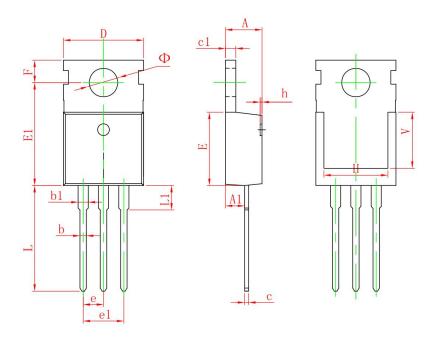


Figure 11 Normalized Maximum Transient Thermal Impedance

TO-220-3L Package Information



Cumbal	Dimensions	In Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
Α	4.400	4.600	0.173	0.181	
A1	2.250	2.550	0.089	0.100	
b	0.710	0.910	0.028	0.036	
b1	1.170	1.370	0.046	0.054	
С	0.330	0.650	0.013	0.026	
c1	1.200	1.400	0.047	0.055	
D	9.910	10.250	0.390	0.404	
E	8.950	9.750	0.352	0.384	
E1	12.650	13.050	0.498	0.514	
е	2.540	TYP.	0.100 TYP.		
e1	4.980	5.180	0.196	0.204	
F	2.650	2.950	0.104	0.116	
Н	7.900	8.100	0.311	0.319	
h	0.000	0.300	0.000	0.012	
L	12.900	13.400	0.508	0.528	
L1	2.850	3.250	0.112	0.128	
V	6.900 REF.		0.276	REF.	
Φ	3.400	3.800	0.134	0.150	

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